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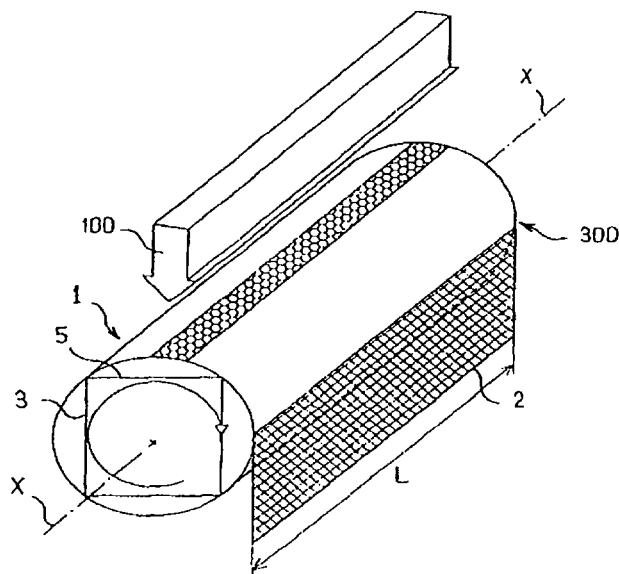
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(54) Title: METHOD AND DEVICE FOR MAKING SUBSTRATES

(54) Titre : PROCEDE ET DISPOSITIF DE FABRICATION DE SUBSTRATS



(57) Abstract: The invention concerns a method for making substrates, in particular for optics, electronics or optoelectronics, characterised in that it comprises an operation which consists in implanting (100) atomic species beneath the surface of a material in the form of a cylindrical ingot (1), at a depth of implantation distributed about a certain value by bombardment of said atomic species on a zone of the ingot (1) cylindrical surface, and an operation which consists in removing (300), at a separation depth located proximate to the depth of implantation, the layer (2) of material located between the surface and the separation depth, to remove said layer (2) from the rest of the ingot (1).

(57) Abrégé : L'invention concerne un procédé de fabrication de substrats, notamment pour l'optique, l'électronique ou l'optoélectronique, caractérisé par le fait qu'il comprend, une opération consistant à implanter (100) des espèces atomiques sous la surface d'un matériau sous la forme d'un lingot (1) cylindrique, à une profondeur d'implantation distribuée autour d'une certaine valeur en bombardant ces espèces atomiques sur une zone de la surface cylindrique du lingot (1), et une opération de détachement (300), au niveau d'une profondeur de décollement située au voisinage de la profondeur d'implantation, de la couche (2) de matériau située entre la surface et la profondeur de décollement, pour détacher cette couche (2) du reste du lingot (1).



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